

## **VL5001 DEVICE MODELING – I**

### DETAILED SYLLABUS

#### **UNIT I MOS CAPACITORS**

Surface Potential: Accumulation, Depletion, and Inversion, Electrostatic Potential and Charge Distribution in Silicon, Capacitances in an MOS Structure, Polysilicon-Gate Work Function and Depletion Effects, MOS under Nonequilibrium and Gated Diodes, Charge in Silicon Dioxide and at the Silicon–Oxide Interface, Effect of Interface Traps and Oxide Charge on Device Characteristics, High-Field Effects, Impact Ionization and Avalanche Breakdown, Band-to-Band Tunneling, Tunneling into and through Silicon Dioxide, Injection of Hot Carriers from Silicon into Silicon Dioxide, High-Field Effects in Gated Diodes, Dielectric Breakdown

#### **UNIT II MOSFET DEVICES**

Long-Channel MOSFETs, Drain-Current Model, MOSFET I–V Characteristics, Subthreshold Characteristics, Substrate Bias and Temperature Dependence of Threshold Voltage, MOSFET Channel Mobility, MOSFET Capacitances and Inversion-Layer Capacitance Effect, Short-Channel MOSFETs, Short-Channel Effect, Velocity Saturation and High-Field Transport Channel Length Modulation, Source–Drain Series Resistance, MOSFET Degradation and Breakdown at High Fields

#### **UNIT III CMOS DEVICE DESIGN**

MOSFET Scaling, Constant-Field Scaling, Generalized Scaling, Non scaling Effects, Threshold Voltage, Threshold-Voltage Requirement, Channel Profile Design, Nonuniform Doping, Quantum Effect on Threshold Voltage, Discrete Dopant Effects on Threshold Voltage, MOSFET Channel Length, Various Definitions of Channel Length, Extraction of the Effective Channel Length, Physical Meaning of Effective Channel Length, Extraction of Channel Length by C–V Measurements

#### **UNIT IV CMOS PERFORMANCE FACTORS**

Basic CMOS Circuit Elements, CMOS Inverters, CMOS NAND and NOR Gates, Inverter and NAND Layouts, Parasitic Elements, Source–Drain Resistance, Parasitic Capacitances, Gate Resistance, Interconnect R and C, Sensitivity of CMOS Delay to Device Parameters, Propagation Delay and Delay Equation, Delay Sensitivity to Channel Width, Length, and Gate Oxide Thickness, Sensitivity of Delay to Power-Supply Voltage and Threshold Voltage, Sensitivity of Delay to Parasitic Resistance and Capacitance, Delay of Two-Way NAND and Body Effect, Performance Factors of Advanced CMOS Devices, MOSFETs in RF Circuits, Effect of Transport Parameters on CMOS Performance, Low-Temperature CMOS

#### **UNIT V BIPOLAR DEVICES**

n–p–n Transistors, Basic Operation of a Bipolar Transistor, Modifying the Simple Diode Theory for Describing Bipolar Transistors, Ideal Current–Voltage Characteristics, Collector Current, Base Current, Current Gains, Ideal IC–VCE Characteristics, Characteristics of a Typical n–p–n Transistor, Effect of Emitter and Base Series Resistances, Effect of Base–Collector Voltage on Collector Current, Collector Current Falloff at High Currents, Nonideal Base Current at Low Currents, Bipolar Device Models for Circuit and Time-Dependent Analyses Basic dc Model,

Basic ac Model, Small-Signal Equivalent-Circuit Model, Emitter Diffusion Capacitance, Charge-Control Analysis, Breakdown Voltages, Common-Base Current Gain in the Presence of Base–Collector Junction Avalanche, Saturation Currents in a Transistor, Relation Between BVCEO and BVCBO.

**OBJECTIVES**

- To study the MOS capacitors and to model MOS Transistors
- To understand the various CMOS design parameters and their impact on performance of the device.
- To study the device level characteristics of BJT transistors

**REFERENCES:**

1. Behzad Razavi, "Fundamentals of Microelectronics" Wiley Student Edition, 2nd Edition.
2. J P Collinge, C A Collinge, "Physics of Semiconductor devices" Springer 2002 Edition.
3. Yuan Taur and Tak H. Ning, "Fundamentals of Modern VLSI Devices", Cambridge University Press, Second Edition.